

# SOT-89-3L Plastic-Encapsulate Transistors

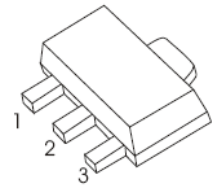
## KTA1273 TRANSISTOR (PNP)

### FEATURES

- High Current
- Low Voltage
- Complementary to KTC3205

### SOT-89-3L

1. BASE
2. COLLECTOR
3. EMITTER



### MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-30	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-30	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-2	A
P <sub>C</sub>	Collector Power Dissipation	500	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	250	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

### ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CB0</sub>	I <sub>C</sub> =-1mA, I <sub>E</sub> =0	-30			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-10mA, I <sub>B</sub> =0	-30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-1mA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-30V, I <sub>E</sub> =0			-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-100	nA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-0.5A	100		320	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-1.5A, I <sub>B</sub> =-30mA			-2	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-2V, I <sub>C</sub> =-500mA		120		MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz		48		pF

### CLASSIFICATION OF h<sub>FE</sub>

RANK	O	Y
RANGE	100 - 200	160 - 320
MARKING	1273	